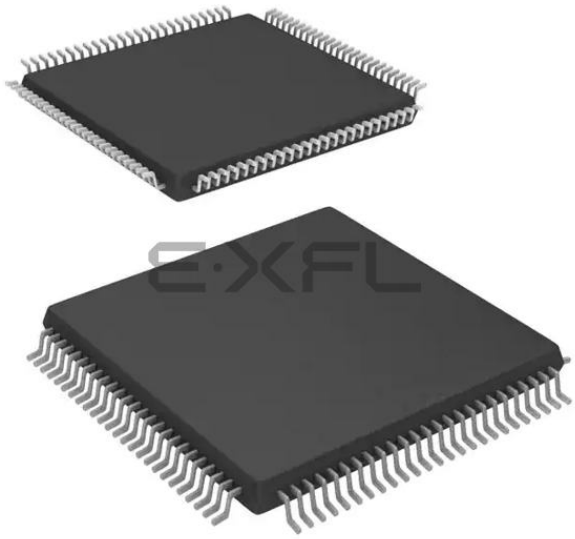

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3072
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln125v5-zvq100

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Flash Advantages

Low Power

Flash-based IGLOO nano devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. IGLOO nano devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

IGLOO nano devices also have low dynamic power consumption to further maximize power savings; power is reduced even further by the use of a 1.2 V core voltage.

Low dynamic power consumption, combined with low static power consumption and Flash*Freeze technology, gives the IGLOO nano device the lowest total system power offered by any FPGA.

Security

Nonvolatile, flash-based IGLOO nano devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOO nano devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOO nano devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of security in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in IGLOO nano devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOO nano devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOO nano devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of IGLOO nano devices. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. IGLOO nano devices, with FlashLock and AES security, are unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOO nano device provides the best available security for programmable logic designs.

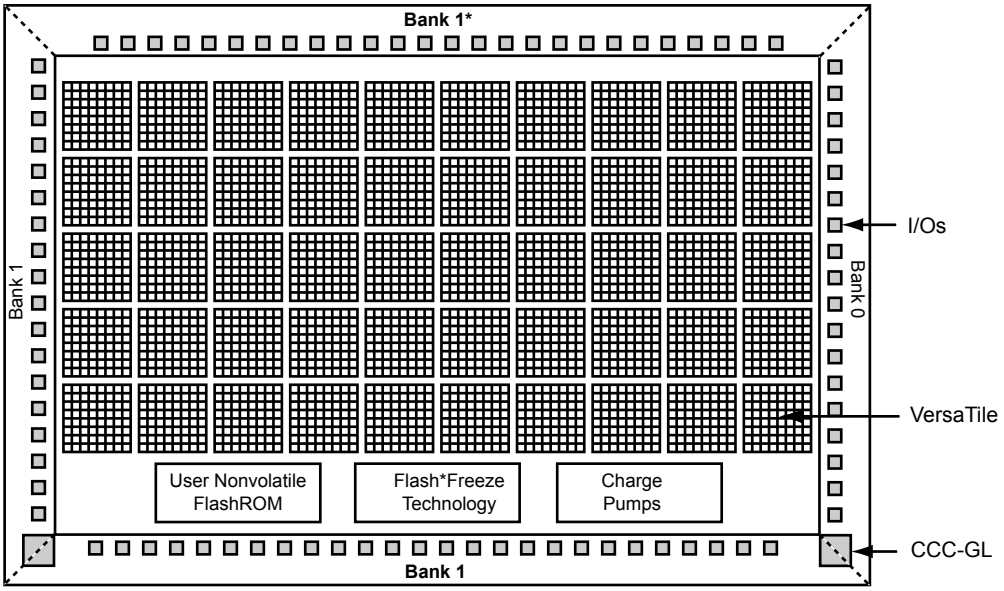
Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOO nano FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Microsemi flash-based IGLOO nano devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOO nano devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOO nano device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOO nano devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

IGLOO nano flash FPGAs enable the user to quickly enter and exit Flash*Freeze mode. This is done almost instantly (within 1 µs) and the device retains configuration and data in registers and RAM. Unlike SRAM-based FPGAs, the device does not need to reload configuration and design state from external memory components; instead it retains all necessary information to resume operation immediately.



*Note: *Bank 0 for the AGLN030 device*

Figure 1-1 • **IGLOO Device Architecture Overview with Two I/O Banks and No RAM (AGLN010 and AGLN030)**

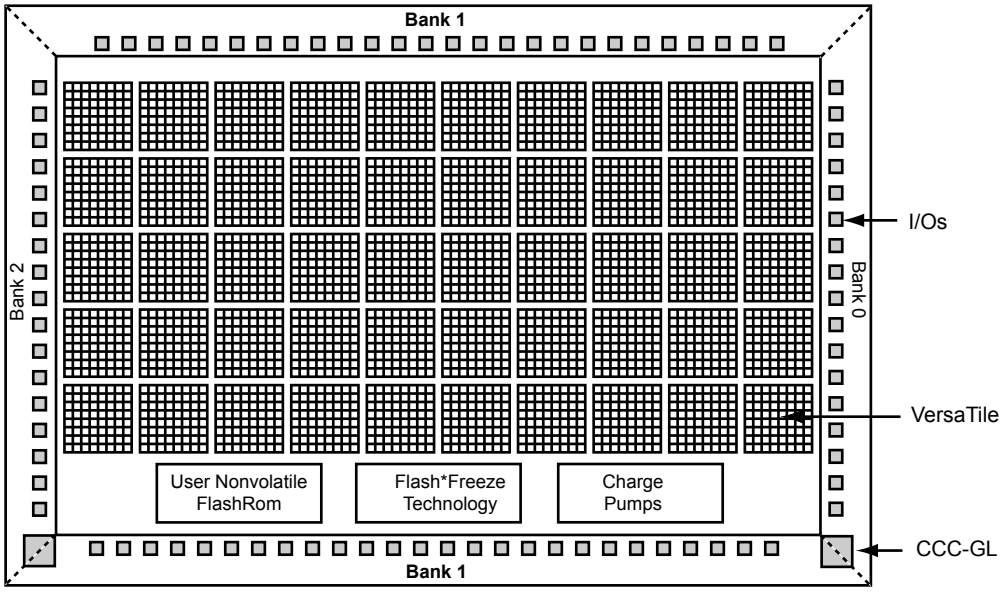


Figure 1-2 • **IGLOO Device Architecture Overview with Three I/O Banks and No RAM (AGLN015 and AGLN020)**

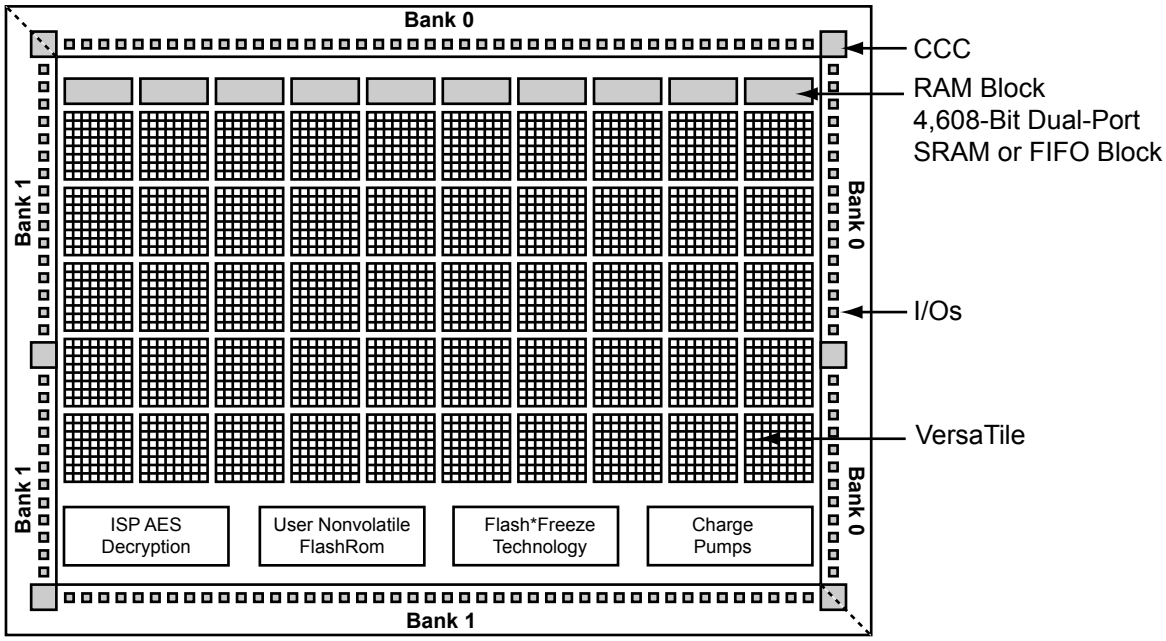


Figure 1-3 • **IGLOO Device Architecture Overview with Two I/O Banks (AGLN060, AGLN125)**

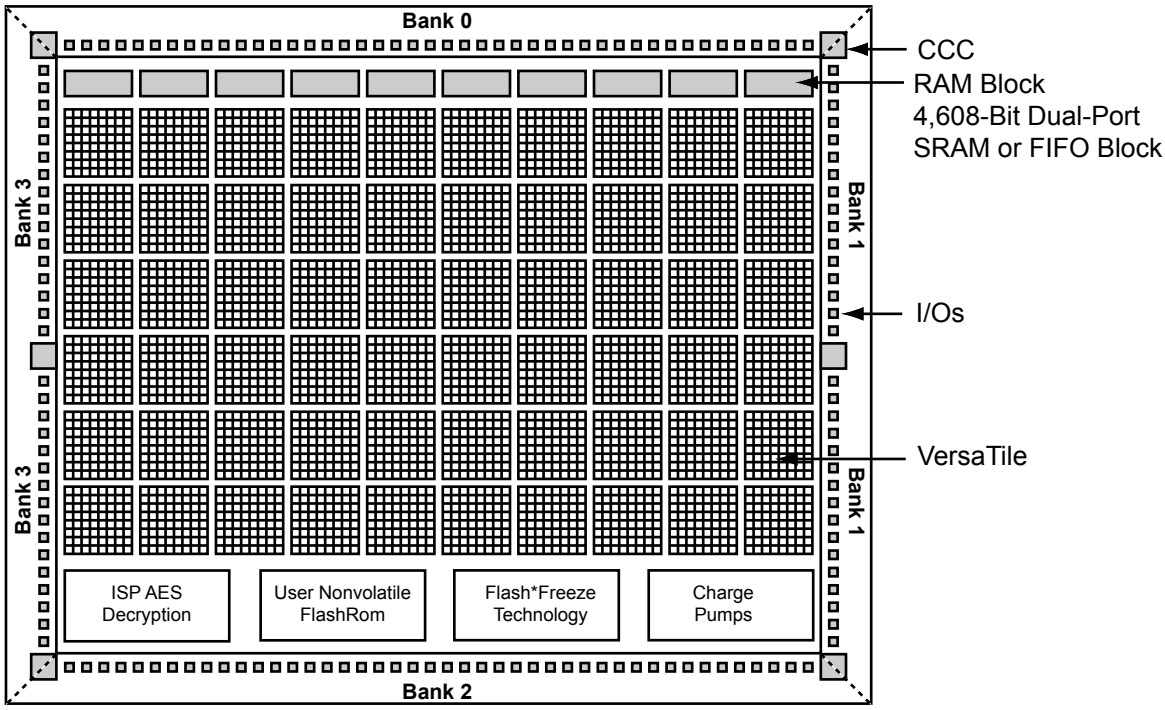


Figure 1-4 • **IGLOO Device Architecture Overview with Four I/O Banks (AGLN250)**

Flash*Freeze Technology

The IGLOO nano device has an ultra-low power static mode, called Flash*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash*Freeze technology enables the user to quickly (within 1 µs) enter and exit Flash*Freeze mode by activating the Flash*Freeze pin while all power supplies are kept at their original values. I/Os, global I/Os, and clocks can still be driven and can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and I/O states. I/Os can be individually configured to either hold their previous state or be tristated during Flash*Freeze mode.

Alternatively, I/Os can be set to a specific state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL, and the device consumes as little as 2 µW in this mode.

Flash*Freeze technology allows the user to switch to Active mode on demand, thus simplifying the power management of the device.

The Flash*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. Refer to Figure 1-5 for an illustration of entering/exiting Flash*Freeze mode. It is also possible to use the Flash*Freeze pin as a regular I/O if Flash*Freeze mode usage is not planned.

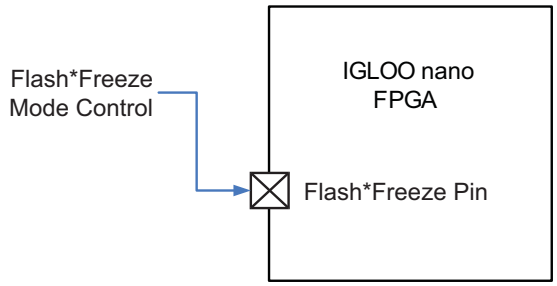


Figure 1-5 • **IGLOO nano Flash*Freeze Mode**

VersaTiles

The IGLOO nano core consists of VersaTiles, which have been enhanced beyond the ProASIC[PLUS]® core tiles. The IGLOO nano VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-6 for VersaTile configurations.

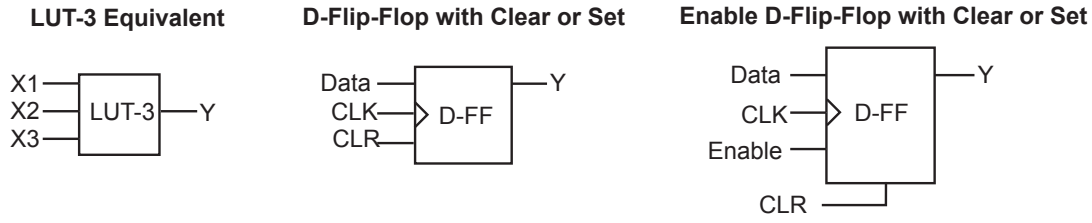


Figure 1-6 • **VersaTile Configurations**

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode*

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
VCCI= 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: *$I_{DD} = N_{BANKS} * I_{CCI}$.

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	0	0	0	0	µA

Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode[1]

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
ICCA Current[2]								
Typical (25°C)	1.2 V	3.7	5	5	10	13	18	µA
	1.5 V	8	14	14	20	28	44	µA
ICCI or IJTAG Current								
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *IDD = N_{BANKS} * ICCI + ICCA. JTAG counts as one bank when powered.*
2. *Includes VCC, VCCPLL, and VPUMP currents.*

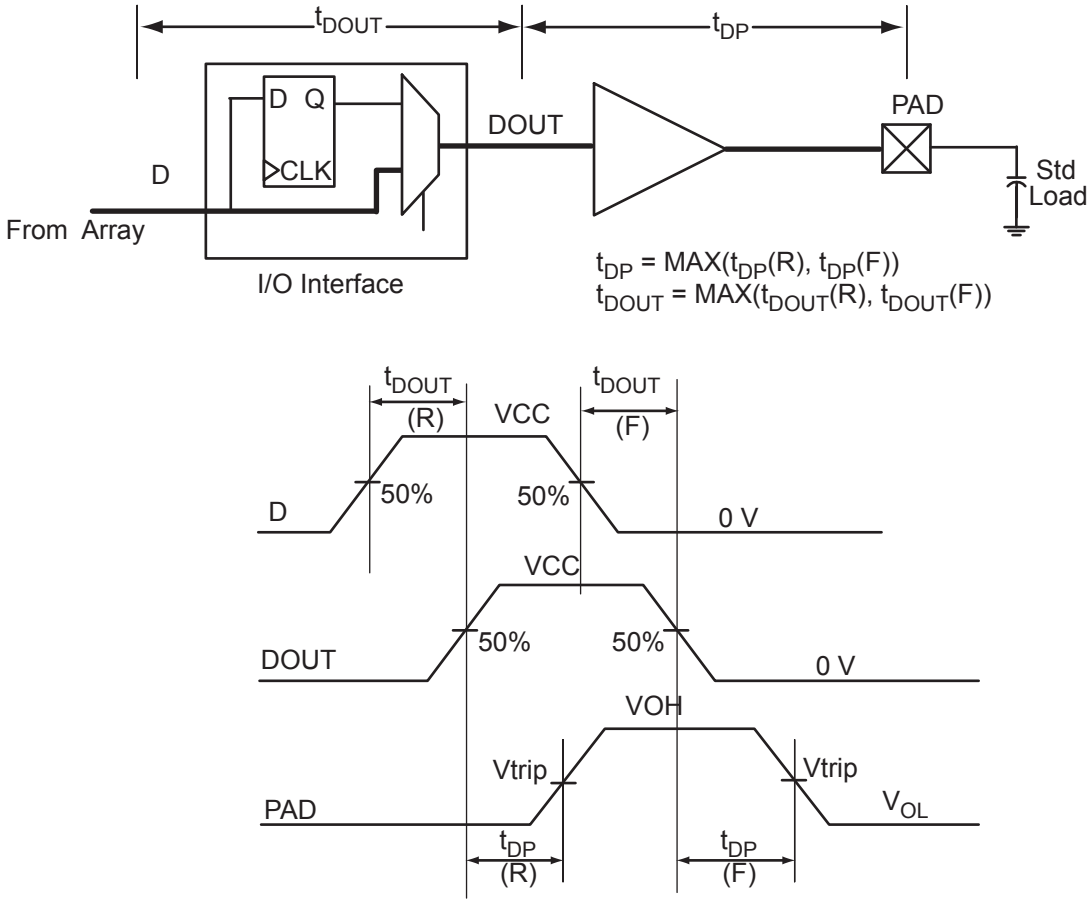


Figure 2-5 • **Output Buffer Model and Delays (example)**

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100 µA	100 µA
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	100 µA	100 µA

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.*
4. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range, as specified in the JESD8-12 specification.*

Table 2-22 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

DC I/O Standards	Commercial[1]		Industrial[2]	
	IIL[3] µA	IIH[4] µA	IIL[3] µA	IIH[4] µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCOMS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS[5]	10	10	15	15
1.2 V LVCMOS Wide Range[5]	10	10	15	15

Notes:

1. *Commercial range (–20°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions, where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions, where –0.3 V < VIN < VIL.*
5. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*

Applies to IGLOO nano at 1.2 V Core Operating Conditions

**Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings
STD Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V**

I/O Standard	Drive Strength (mA)	Equiv. Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY})	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.31	0.26	0.97	1.36	1.10	2.34	1.90	2.43	3.14	ns
3.3 V LVCMOS Wide Range[2]	100 µA	8 mA	High	5 pF	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns
2.5 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.30	0.26	1.21	1.39	1.10	2.33	2.04	2.41	2.99	ns
1.8 V LVCMOS	4 mA	4 mA	High	5 pF	1.55	2.49	0.26	1.13	1.59	1.10	2.53	2.34	2.42	2.81	ns
1.5 V LVCMOS	2 mA	2 mA	High	5 pF	1.55	2.78	0.26	1.27	1.77	1.10	2.82	2.62	2.44	2.74	ns
1.2 V LVCMOS	1 mA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns
1.2 V LVCMOS Wide Range[3]	100 µA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V side range as specified in the JESD8-12 specification.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

VCCI	$R_{(WEAK\ PULL\text{-}UP)}$[1] (Ω)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] (Ω)	
	Min.	Max.	Min.	Max.
3.3 V	10 K	45 K	10 K	45 K
3.3 V (wide range I/Os)	10 K	45 K	10 K	45 K
2.5 V	11 K	55 K	12 K	74 K
1.8 V	18 K	70 K	17 K	110 K
1.5 V	19 K	90 K	19 K	140 K
1.2 V	25 K	110 K	25 K	150 K
1.2 V (wide range I/Os)	19 K	110 K	19 K	150 K

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)} = (VCCImax - VOHspec) / I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

Table 2-30 • I/O Short Currents IOSH/IOSL

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
3.3 V LVCMOS Wide Range	100 µA	Same as equivalent software default drive	
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
1.5 V LVCMOS	2 mA	13	16
1.2 V LVCMOS	1 mA	10	13
1.2 V LVCMOS Wide Range	100 µA	10	13

*Note: *T_J = 100°C*

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general purpose 2.5 V applications.

Table 2-45 • Minimum and Maximum DC Input and Output Levels

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	Min., V	Max., V	Min., V	Max., V	Max., V	Min., V	mA	mA	Max., mA[3]	Max., mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.7	1.7	3.6	0.7	1.7	2	2	16	18	10	10
4 mA	–0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	10	10
6 mA	–0.3	0.7	1.7	3.6	0.7	1.7	6	6	32	37	10	10
8 mA	–0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	10	10

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

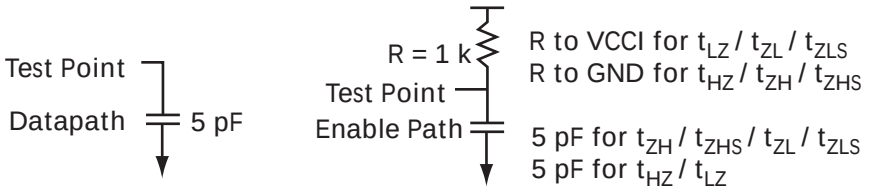


Figure 2-8 • AC Loading

Table 2-46 • 2.5 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	2.5	1.2	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-57 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA [3]	Max. mA [3]	µA [4]	µA [4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

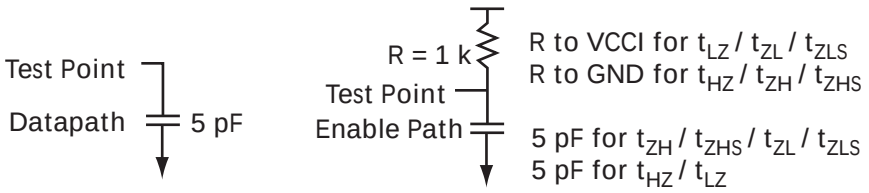


Figure 2-10 • AC Loading

Table 2-58 • 1.5 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.5	0.75	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

I/O Register Specifications

Fully Registered I/O Buffers with Asynchronous Preset

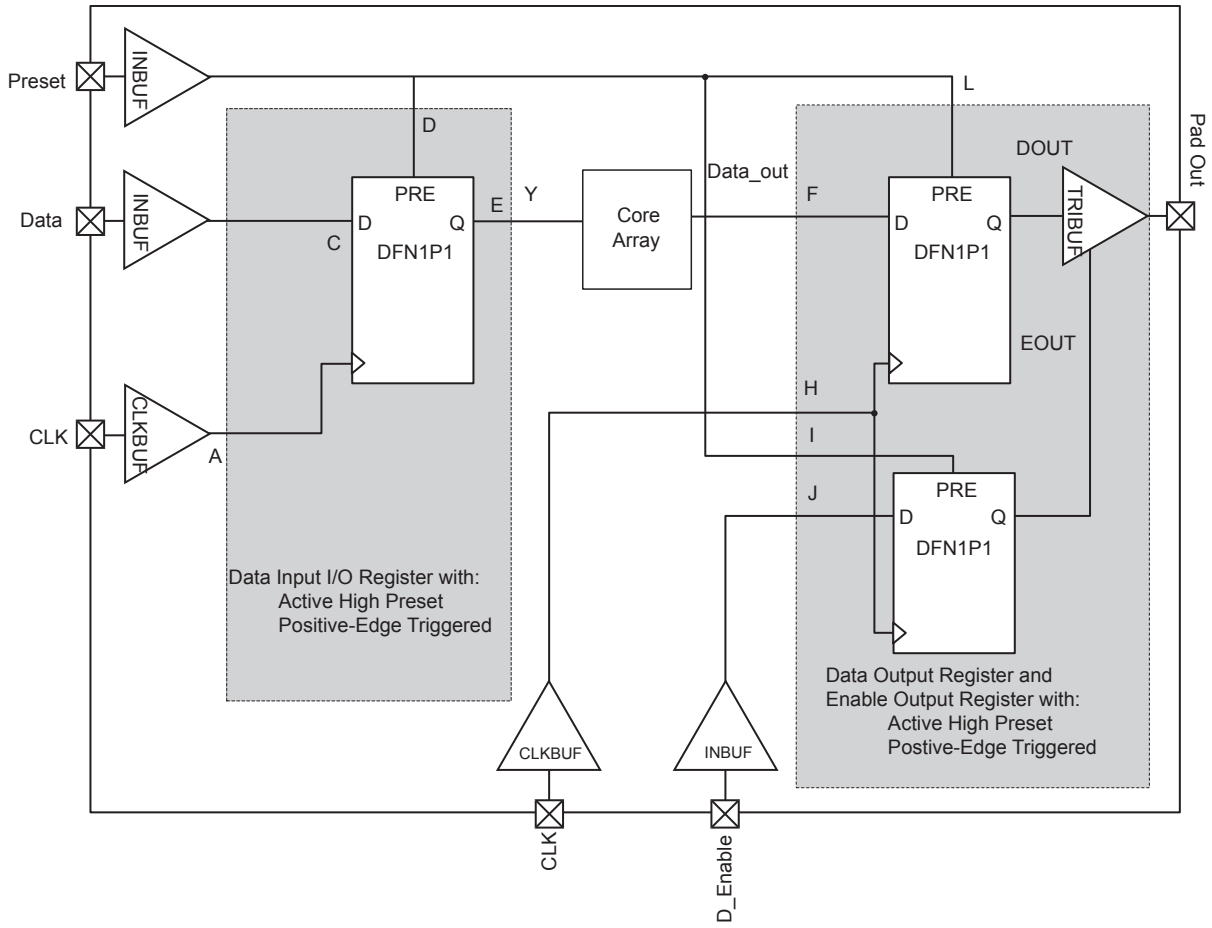


Figure 2-12 • **Timing Model of Registered I/O Buffers with Asynchronous Preset**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-84 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y = !A	t_{PD}	0.76	ns
AND2	Y = A · B	t_{PD}	0.87	ns
NAND2	Y = !(A · B)	t_{PD}	0.91	ns
OR2	Y = A + B	t_{PD}	0.90	ns
NOR2	Y = !(A + B)	t_{PD}	0.94	ns
XOR2	Y = A ⊕ B	t_{PD}	1.39	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	1.44	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	1.60	ns
MUX2	Y = A !S + B S	t_{PD}	1.17	ns
AND3	Y = A · B · C	t_{PD}	1.18	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-85 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y = !A	t_{PD}	1.33	ns
AND2	Y = A · B	t_{PD}	1.48	ns
NAND2	Y = !(A · B)	t_{PD}	1.58	ns
OR2	Y = A + B	t_{PD}	1.53	ns
NOR2	Y = !(A + B)	t_{PD}	1.63	ns
XOR2	Y = A ⊕ B	t_{PD}	2.34	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	2.59	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	2.74	ns
MUX2	Y = A !S + B S	t_{PD}	2.03	ns
AND3	Y = A · B · C	t_{PD}	2.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-87 • Register Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	1.61	ns
t_{SUD}	Data Setup Time for the Core Register	1.17	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	1.29	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Core Register	0.95	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-92 • AGLN125 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-93 • AGLN250 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

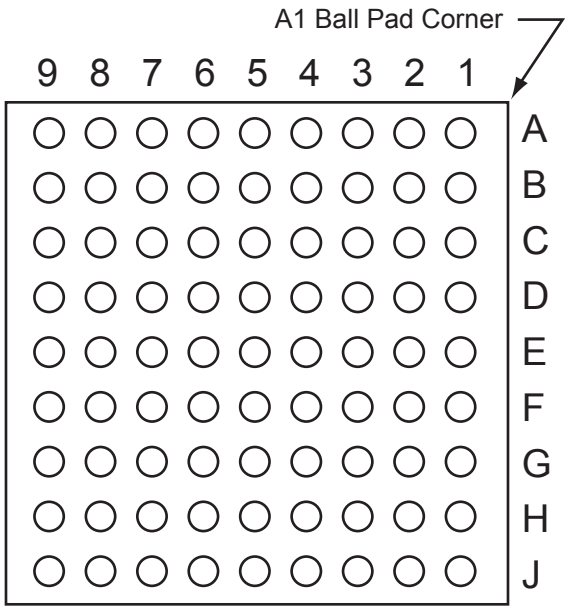
Table 2-106 • FIFO

Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.66	ns
t_{ENH}	REN, WEN Hold Time	0.13	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.63	ns
t_{DH}	Input Data (WD) Hold Time	0.20	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.77	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.50	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.94	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.79	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	10.71	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.90	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
t_{RSTBQ}	RESET Low to Data Out LOW on RD (flow-through)	1.68	ns
	RESET Low to Data Out LOW on RD (pipelined)	1.68	ns
$t_{REMRSTB}$	RESET Removal	0.51	ns
$t_{RECRSTB}$	RESET Recovery	2.68	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

CS81



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

CS81	
Pin Number	AGLN125 Function
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO13RSB0
A5	IO22RSB0
A6	IO32RSB0
A7	GBB0/IO37RSB0
A8	GBA1/IO40RSB0
A9	GBA2/IO41RSB0
B1	GAA2/IO132RSB1
B2	GAB0/IO02RSB0
B3	GAC1/IO05RSB0
B4	IO11RSB0
B5	IO25RSB0
B6	GBC0/IO35RSB0
B7	GBB1/IO38RSB0
B8	IO42RSB0
B9	GBB2/IO43RSB0
C1	GAB2/IO130RSB1
C2	IO131RSB1
C3	GND
C4	IO15RSB0
C5	IO28RSB0
C6	GND
C7	GBA0/IO39RSB0
C8	GBC2/IO45RSB0
C9	IO47RSB0
D1	GAC2/IO128RSB1
D2	IO129RSB1
D3	GFA2/IO117RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO59RSB0
D8	GCC1/IO51RSB0
D9	GCC0/IO52RSB0

CS81	
Pin Number	AGLN125 Function
E1	GFB0/IO120RSB1
E2	GFB1/IO121RSB1
E3	GFA1/IO118RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GCA0/IO56RSB0
E8	GCA1/IO55RSB0
E9	GCB2/IO58RSB0
F1*	VCCPLF
F2*	VCOMPLF
F3	GND
F4	GND
F5	VCCIB1
F6	GND
F7	GDA1/IO65RSB0
F8	GDC1/IO61RSB0
F9	GDC0/IO62RSB0
G1	GEA0/IO104RSB1
G2	GEC0/IO108RSB1
G3	GEB1/IO107RSB1
G4	IO96RSB1
G5	IO92RSB1
G6	IO72RSB1
G7	GDB2/IO68RSB1
G8	VJTAG
G9	TRST
H1	GEA1/IO105RSB1
H2	FF/GEB2/IO102RSB1
H3	IO99RSB1
H4	IO94RSB1
H5	IO91RSB1
H6	IO81RSB1
H7	GDA2/IO67RSB1
H8	TDI
H9	TDO

CS81	
Pin Number	AGLN125 Function
J1	GEA2/IO103RSB1
J2	GEC2/IO101RSB1
J3	IO97RSB1
J4	IO93RSB1
J5	IO90RSB1
J6	IO78RSB1
J7	TCK
J8	TMS
J9	VPUMP

*Note: * Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN125-CS81.*

VQ100	
Pin Number	AGLN060Z Function
1	GND
2	GAA2/IO51RSB1
3	IO52RSB1
4	GAB2/IO53RSB1
5	IO95RSB1
6	GAC2/IO94RSB1
7	IO93RSB1
8	IO92RSB1
9	GND
10	GFB1/IO87RSB1
11	GFB0/IO86RSB1
12	VCOMPLF
13	GFA0/IO85RSB1
14	VCCPLF
15	GFA1/IO84RSB1
16	GFA2/IO83RSB1
17	VCC
18	VCCIB1
19	GEC1/IO77RSB1
20	GEB1/IO75RSB1
21	GEB0/IO74RSB1
22	GEA1/IO73RSB1
23	GEA0/IO72RSB1
24	VMV1
25	GNDQ
26	GEA2/IO71RSB1
27	FF/GEB2/IO70RSB1
28	GEC2/IO69RSB1
29	IO68RSB1
30	IO67RSB1
31	IO66RSB1
32	IO65RSB1
33	IO64RSB1
34	IO63RSB1

VQ100	
Pin Number	AGLN060Z Function
35	IO62RSB1
36	IO61RSB1
37	VCC
38	GND
39	VCCIB1
40	IO60RSB1
41	IO59RSB1
42	IO58RSB1
43	IO57RSB1
44	GDC2/IO56RSB1
45*	GDB2/IO55RSB1
46	GDA2/IO54RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO49RSB0
58	GDC0/IO46RSB0
59	GDC1/IO45RSB0
60	GCC2/IO43RSB0
61	GCB2/IO42RSB0
62	GCA0/IO40RSB0
63	GCA1/IO39RSB0
64	GCC0/IO36RSB0
65	GCC1/IO35RSB0
66	VCCIB0
67	GND
68	VCC

VQ100	
Pin Number	AGLN060Z Function
69	IO31RSB0
70	GBC2/IO29RSB0
71	GBB2/IO27RSB0
72	IO26RSB0
73	GBA2/IO25RSB0
74	VMV0
75	GNDQ
76	GBA1/IO24RSB0
77	GBA0/IO23RSB0
78	GBB1/IO22RSB0
79	GBB0/IO21RSB0
80	GBC1/IO20RSB0
81	GBC0/IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO15RSB0
85	IO13RSB0
86	IO11RSB0
87	VCCIB0
88	GND
89	VCC
90	IO10RSB0
91	IO09RSB0
92	IO08RSB0
93	GAC1/IO07RSB0
94	GAC0/IO06RSB0
95	GAB1/IO05RSB0
96	GAB0/IO04RSB0
97	GAA1/IO03RSB0
98	GAA0/IO02RSB0
99	IO01RSB0
100	IO00RSB0

*Note: *The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin 45 in AGLN060Z-VQ100.*